

(19) World Intellectual Property Organization
International Bureau



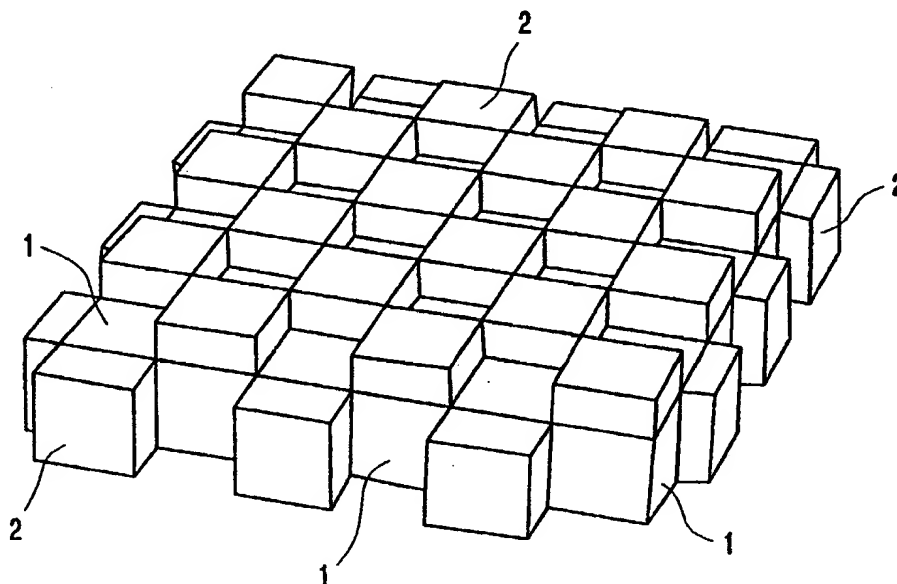
(43) International Publication Date
20 September 2001 (20.09.2001)

PCT

(10) International Publication Number
WO 01/69692 A1

- (51) International Patent Classification⁷: H01L 33/00 (74) Agent: MULDER, Cornelis, A., M.; Internationaal Octrooibureau B.V., Prof Holstlaan 6, NL-5656 AA Eindhoven (NL).
- (21) International Application Number: PCT/EP01/02430
- (22) International Filing Date: 5 March 2001 (05.03.2001) (81) Designated States (*national*): CN, JP.
- (25) Filing Language: English (84) Designated States (*regional*): European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR).
- (26) Publication Language: English
- (30) Priority Data: 00200922.3 14 March 2000 (14.03.2000) EP
Published:
— with international search report
— before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments
- (71) Applicant: LUMILEDS LIGHTING B.V. [NL/NL]; De Rijn 2, NL-5680 AK Best (NL).
- (72) Inventor: KEUPER, Matthijs, H.; Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).
- For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.*

(54) Title: LIGHT-EMITTING DIODE, LIGHTING DEVICE AND METHOD OF MANUFACTURING SAME



(57) Abstract: A light-emitting diode comprises a chip (1) emitting visible light of a first wavelength, a light-emitting surface and a phosphor layer provided on the light-emitting surface. Said phosphor layer is capable of converting light of the first wavelength to visible light of a second wavelength. According to the invention, a part of the light-emitting surface is not covered with the phosphor layer. Preferably, the size of said surface is chosen to be such that by mixing emitted light of the first and the second wavelength substantially white light is obtained. Preferably, the surface that is not covered with the phosphor layer comprises a plurality of sub-surfaces, preferably arranged in the form of a pattern.

WO 01/69692 A1

Light-emitting diode, lighting device and method of manufacturing same

The invention relates to a light-emitting diode comprising a chip capable of emitting visible light of a first wavelength, a light-emitting surface and a phosphor layer which is provided on the light-emitting surface and which is capable of converting light of the first wavelength to visible light of a second wavelength.

5 Such a light-emitting diode (LED) is well known. In the case of an LED, the chip emits colored light of one specific wavelength. Hitherto, LEDs were predominantly used as signal lamps, but as a result of the increased light output, LEDs are increasingly used, at present, to illuminate objects. In many applications there is a trend towards illuminating an object with light of a different color, particularly light comprising different wavelengths, for
10 example substantially white light, which is the reason why the light-emitting surface of the known LED is provided with a phosphor layer which partially absorbs the light (of a short wavelength) which is emitted by the chip and converts said light to light of a different (longer) wavelength. By providing the phosphor layer in a thickness such that only an accurately determined part of the light emitted by the chip is converted to said other color,
15 the desired result, for example substantially white light, can be achieved as a result of the fact that both colors mix.

 The above-described LED has the disadvantage that in order to obtain a light output having a predetermined, accurate color temperature, the thickness of the phosphor layer must be very accurately controlled, which is a complex process. As a result, in practice,
20 variations in the thickness of this layer occur, which may lead to undesirable color deviations, which may range from several thousand to several hundred Kelvin in color temperature.

 WO 98/39805 discloses a light-emitting diode whose light-emitting surface is surrounded by a transparent mass comprising a mixture of three different types of phosphor emitting, respectively, blue, green and red light. By accurately controlling the composition of
25 the phosphor mixture, light of the desired color can be obtained. A drawback of this diode resides in that a large quantity of the phosphor mass must be cast around the chip because all the (ultraviolet) light emitted by the chip must be converted to visible light.

 It is an object of the invention to provide a light-emitting diode having a high light output and a small light-emitting surface, which light-emitting diode is cheap and

simple to manufacture, and which enables light of an accurately defined light temperature to be obtained.

To achieve this, in accordance with the invention, the light-emitting surface comprises a sub-surface without the phosphor layer. From the sub-surface without the phosphor layer issues light (preferably blue light) of the first wavelength (for example approximately 480 nm), which corresponds to the light emitted by the chip (preferably an InGaN chip), and from the sub-surface with the phosphor layer issues the converted light (preferably yellow light) of the second wavelength (for example approximately 575 nm). If both colors mix, light of a different color is obtained. Consequently, the color temperature can be accurately controlled by the choice of the size of the sub-surface. In a preferred embodiment, the size of the sub-surface is such that mixing the emitted light of the first and the second wavelength results in substantially white light. If necessary, a third sub-surface can be covered with a layer of a second type of phosphor which emits light of a third wavelength. In this manner, any desired color can be accurately obtained.

Preferably, the phosphor layer is provided on the diode by means of a well-established technique such as screen printing.

Preferably, the thickness of the phosphor layer is such that all the light of the first wavelength incident on the phosphor layer is converted to light of the second wavelength. As a result, unlike the prior art, the thickness of the phosphor layer does not influence the color temperature.

Preferably, the sub-surface without a phosphor layer, or the sub-surface on which the phosphor layer is provided, is distributed over a plurality of partial sub-surfaces, said partial sub-surfaces preferably forming a pattern, such as a simple chessboard pattern. This pattern is preferably very finely distributed, so that a good mixture of the light is obtained. In certain applications, too coarse a pattern may cause the color pattern to be undesirably projected on the object to be illuminated. To further reduce this effect, a lighting unit wherein a light-emitting diode in accordance with the invention is incorporated preferably comprises optical elements to mix the emitted light of the first and the second wavelength.

In a preferred embodiment, the sub-surface without a phosphor layer is at least partly covered with a light-transmitting layer, which is capable of spreading light incident on said sub-surface. Preferably, the thickness of the light-transmitting layer is the same as that of the phosphor layer, so that the outermost surface of the diode is a flat surface.

The invention also relates to a lighting device comprising at least one light-emitting diode including a chip which is capable of emitting visible light of a first wavelength, a light-emitting surface and a phosphor layer which is provided on the light-emitting surface and which is capable of converting light of the first wavelength to visible light of a second wavelength, said light-emitting surface comprising a sub-surface without the phosphor layer.

The invention also relates to a method of manufacturing a light-emitting diode, wherein a chip, which is capable of emitting visible light of a first wavelength, is at least partly surrounded by a light-emitting surface, and a phosphor layer is provided on the light-emitting surface, which phosphor layer is capable of converting light of the first wavelength to visible light of a second wavelength, and the phosphor layer is removed from, or not provided on, a sub-surface of the light-emitting surface.

These and other aspects of the invention will be apparent from and elucidated with reference to the embodiment(s) described hereinafter.

In the drawings:

Fig. 1 diagrammatically shows a light-emitting diode.

As shown in Fig. 1, a light-emitting diode comprises an InGaN chip 1 having a light-emitting chip surface. On the lower side of the chip there are electric connectors. A phosphor layer is applied to the chip surface by means of screen printing. In this example, said layer is formed by small phosphor blocks 2, which are arranged in accordance with a chessboard pattern. The surface of the chip covered with the phosphor blocks 2 forms the covered sub-surface of the chip, the surface covered by an individual block 2 being referred to as a partial sub-surface. The phosphor layer may be, for example, a TG:Eu phosphor.

If an electric voltage is applied to the InGaN chip, then this chip emits blue light of a wavelength of approximately 480 nm. Subsequently, the blue light issues freely to the exterior through the uncovered sub-surface. The blue light incident on the sub-surface covered with the phosphor blocks 2, however, is absorbed by the phosphor blocks and converted to yellow light of a wavelength of approximately 575 nm. The phosphor layer is sufficiently thick, so that all of the blue light incident thereon is converted to yellow light. Subsequently, this yellow light also issues to the exterior and can mix with the blue light.

Since the phosphor pattern on the diode is very fine, the human eye will not distinguish the two colors issuing from the diode, but will observe only one mixed color, in

this case a substantially white light. By varying the ratio between the phosphor-covered sub-surface and the uncovered sub-surface, different color temperatures can be achieved. In this example, said ratio is 1:1.

5 In some applications, the light issuing from the diode is projected onto an object by means of lenses, in which case enlargement may still lead to undesirable color-separation effects. This can be precluded by accommodating optical elements in the lighting device, which mix light of the two colors.

CLAIMS:

- 1 A light-emitting diode comprising:
a chip capable of emitting visible light of a first wavelength,
a light-emitting surface, and
a phosphor layer which is provided on the light-emitting surface and which is
5 capable of converting light of the first wavelength to visible light of a second wavelength,
characterized in that the light-emitting surface comprises a sub-surface without the phosphor
layer.
2. A diode as claimed in claim 1, characterized in that the size of the sub-surface
10 is such that mixing the emitted light of the first and the second wavelength results in
substantially white light.
3. A diode as claimed in claim 1 or 2, characterized in that the thickness of the
phosphor layer is such that all the light of the first wavelength incident on the phosphor layer
15 is converted to light of the second wavelength.
4. A diode as claimed in claim 1, 2 or 3, characterized in that the sub-surface
without a phosphor layer, or the sub-surface on which the phosphor layer is provided, is
distributed over a plurality of partial sub-surfaces.
20
5. A diode as claimed in claim 4, characterized in that the partial sub-surfaces
form a pattern.
6. A diode as claimed in any one of the preceding claims, characterized in that
25 the sub-surface without a phosphor layer is at least partly covered with a light-transmitting
layer which is capable of spreading light incident on said sub-surface.
- 7 A lighting device comprising at least one light-emitting diode including:
a chip which is capable of emitting visible light of a first wavelength,

a light-emitting surface, and

a phosphor layer which is provided on the light-emitting surface and which is capable of converting light of the first wavelength to visible light of a second wavelength, characterized in that said light-emitting surface comprises a sub-surface without the phosphor layer.

8. A lighting device as claimed in claim 7, characterized in that the lighting unit further comprises optical elements for mixing the emitted light of the first and the second wavelength.

9. A method of manufacturing a light-emitting diode, wherein a chip which is capable of emitting visible light of a first wavelength is at least partly surrounded by a light-emitting surface, and a phosphor layer is provided on the light-emitting surface, which phosphor layer is capable of converting light of the first wavelength to visible light of a second wavelength, characterized in that the phosphor layer is removed from, or not provided on, a sub-surface of the light-emitting surface.

10. A method as claimed in claim 9, characterized in that the phosphor layer is provided on the diode by means of screen printing.

1/1

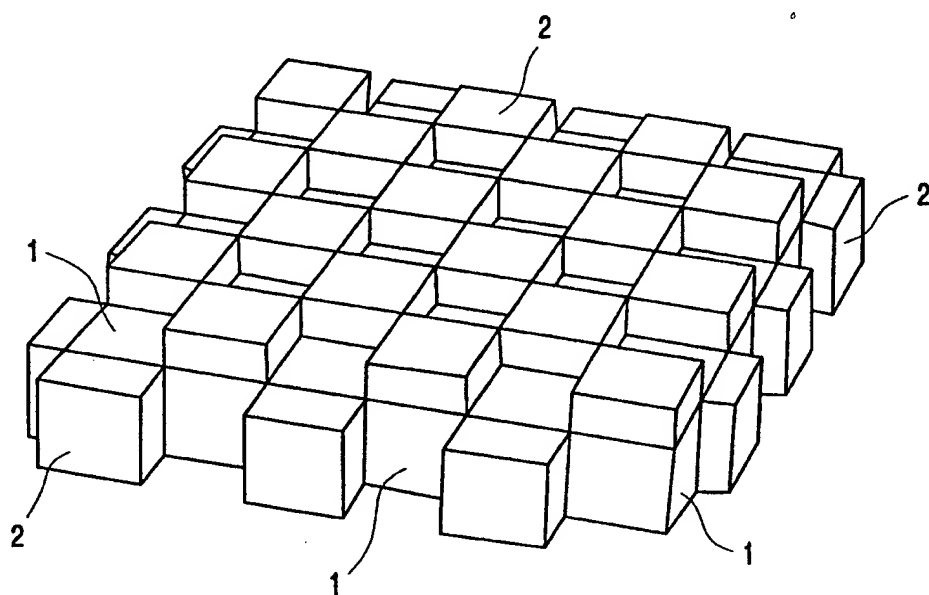


FIG. 1

INTERNATIONAL SEARCH REPORT

International Application No

PCT/EP 01/02430

A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 H01L33/00

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
IPC 7 H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

PAJ, EPO-Internal, WPI Data

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	PATENT ABSTRACTS OF JAPAN vol. 2000, no. 03, 30 March 2000 (2000-03-30) -& JP 11 354847 A (STANLEY ELECTRIC CO LTD), 24 December 1999 (1999-12-24) abstract	1,7-9
A		2,3,10
X	EP 0 855 751 A (INTERNATIONAL BUSINESS MACHINES CORP) 29 July 1998 (1998-07-29) column 7, line 26-38; figure 7A	1-3,9
A		4,5,7

	-/-	

☒ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

* Special categories of cited documents :

- *A* document defining the general state of the art which is not considered to be of particular relevance
- *E* earlier document but published on or after the international filing date
- *L* document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)
- *O* document referring to an oral disclosure, use, exhibition or other means
- *P* document published prior to the international filing date but later than the priority date claimed

- *T* later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
- *X* document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
- *Y* document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art.
- *G* document member of the same patent family

Date of the actual completion of the international search

29 June 2001

Date of mailing of the international search report

06/07/2001

Name and mailing address of the ISA

European Patent Office, P.B. 5818 Patentlaan 2
NL - 2280 HV Rijswijk
Tel. (+31-70) 340-2040, Tx. 31 651 epo nl,
Fax: (+31-70) 340-3016

Authorized officer

De Laere, A

INTERNATIONAL SEARCH REPORT

I. International Application No

PCT/EP 01/02430

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	<p>PATENT ABSTRACTS OF JAPAN vol. 1999, no. 12, 29 October 1999 (1999-10-29) -& JP 11 204832 A (TOSHIBA ELECTRONIC ENGINEERING CORP;TOSHIBA CORP), 30 July 1999 (1999-07-30) abstract</p> <p>---</p>	1-9
A	<p>PATENT ABSTRACTS OF JAPAN vol. 1998, no. 05, 30 April 1998 (1998-04-30) & JP 10 012916 A (HITACHI CABLE LTD), 16 January 1998 (1998-01-16) abstract</p> <p>-----</p>	1,7,9

INTERNATIONAL SEARCH REPORT

Information on patent family members

I. International Application No

PCT/EP 01/02430

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
JP 11354847 A	24-12-1999	NONE	
EP 855751 A	29-07-1998	US 5898185 A US 5895932 A JP 10214992 A	27-04-1999 20-04-1999 11-08-1998
JP 11204832 A	30-07-1999	NONE	
JP 10012916 A	16-01-1998	NONE	